

Mask Industry is Ready for Curvilinear ILT

D2S Confidential and Proprietary
D2S Patented Technology

D2S is a registered trademark of D2S, Inc. in US
TrueMask and TrueModel are registered trademarks of D2S, Inc. in US, Japan, Korea, China and Taiwan

A Decade of ILT!



2005

6 Papers

Foundries

Memory

1 Mask shop



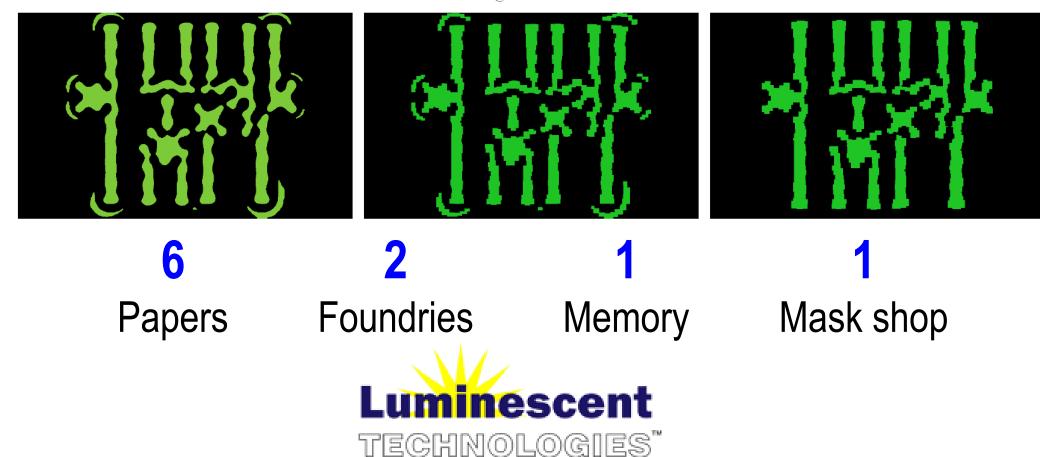
A Decade of ILT!



Fast Inverse Lithography Technology

Daniel S. Abrams, Linyong Pang Luminescent Technologies, Inc., 650 Castro Street, Suite 220, Mountain View, CA 94041, U.S.A.

Email: leo@luminescent.com



ILT Adopted as the Way Forward



>200

Papers





Officially announced















ILT expertise proliferated



2014 panel

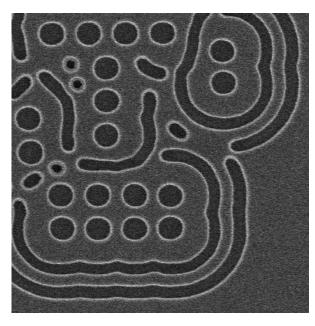
2016 panel





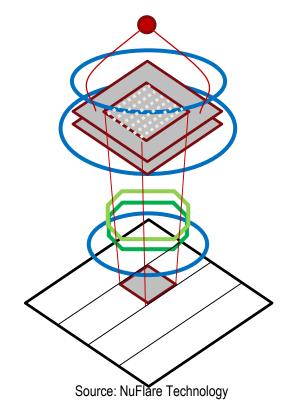
Big Changes Are Coming in Litho and Mask ...



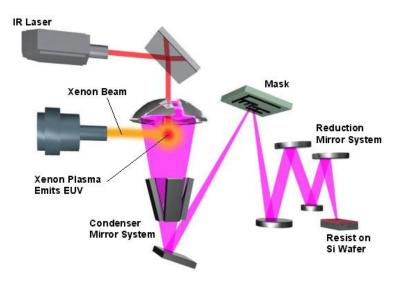


B.G. Kim, et al., BACUS, 2012

ILT Mask Patterns: Here Today



Multi-beam Mask Writing: 2017-2018



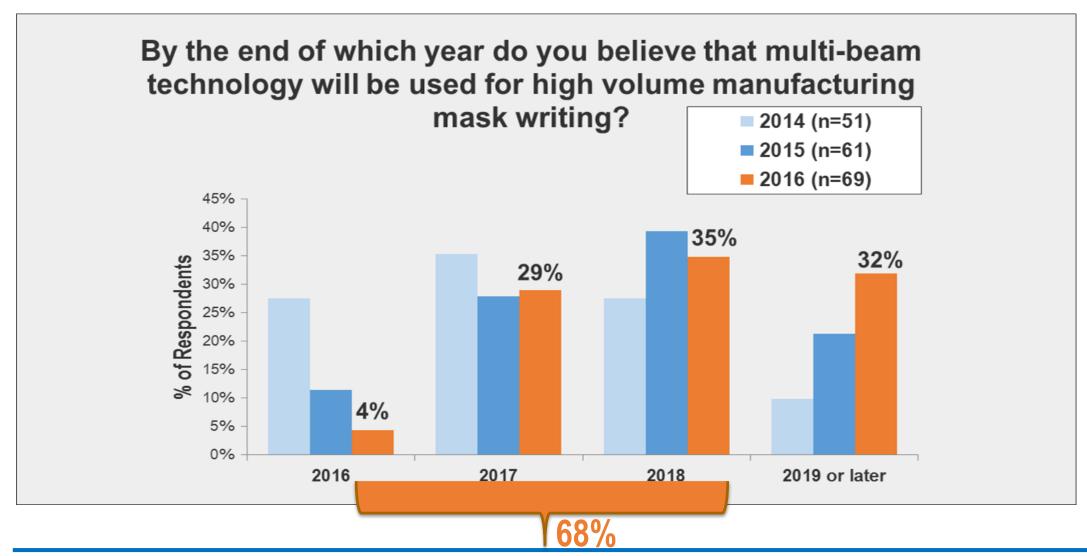
Source: Barrett Research Group

EUV Mask Production: 2018

68% Say Multi-beam HVM by end of 2018

BeamInitiative

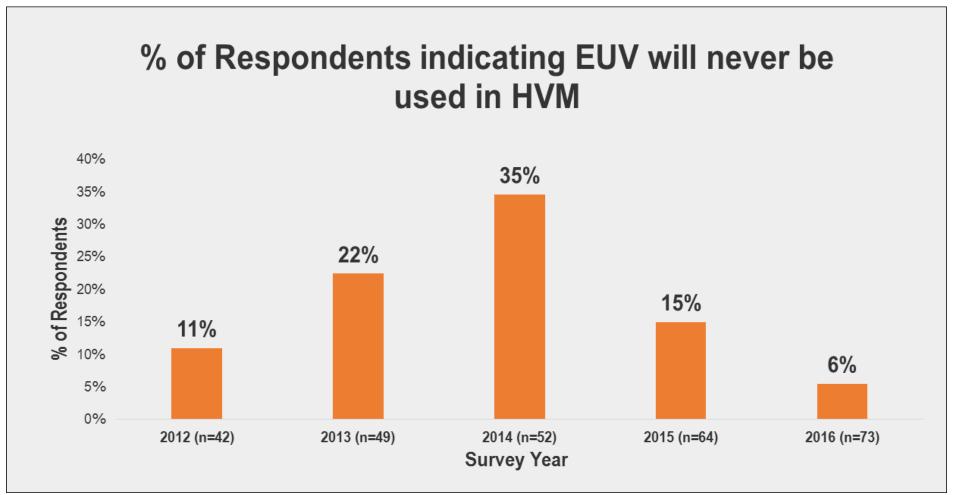
2016 eBeam Initiative Survey



EUV Pessimism is the Lowest in 5 Years

BeamInitiative

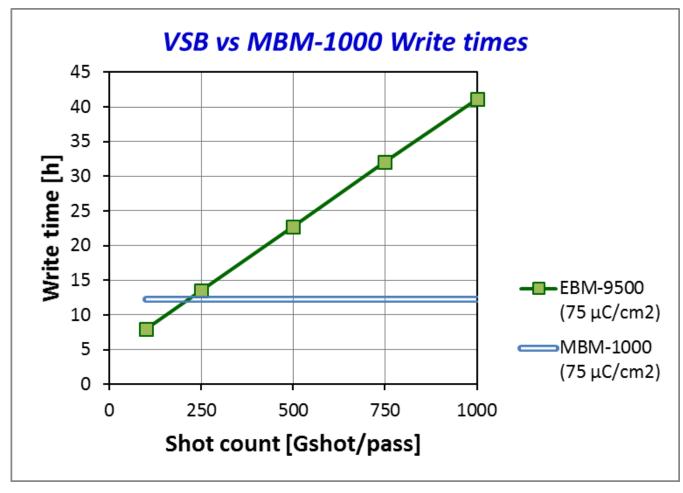
Only 6% Responded with "Never" in 2016



Source: 2016 eBeam Initiative Perceptions Survey www.ebeam.org





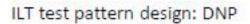


Source: NuFlare Technology, eBeam Initiative SPIE lunch 2016

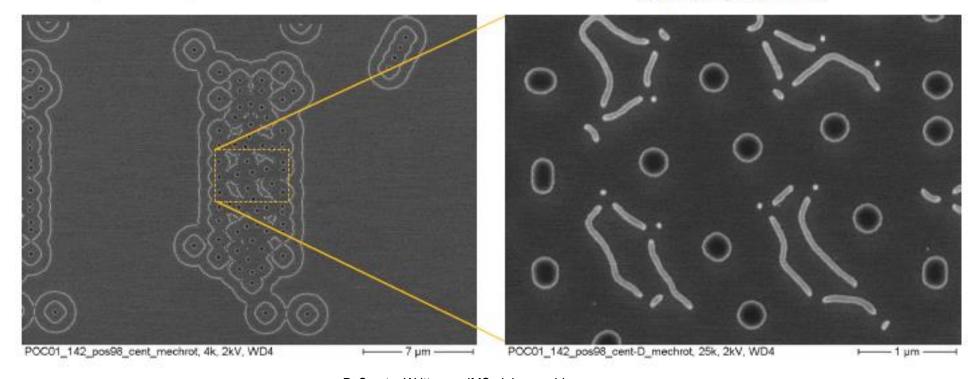
Multi-beam has the shot count advantage > ~200 Gshot/pass

Multi-beam is Great for Curvilinear ILT





50nm dots, 75nm lines

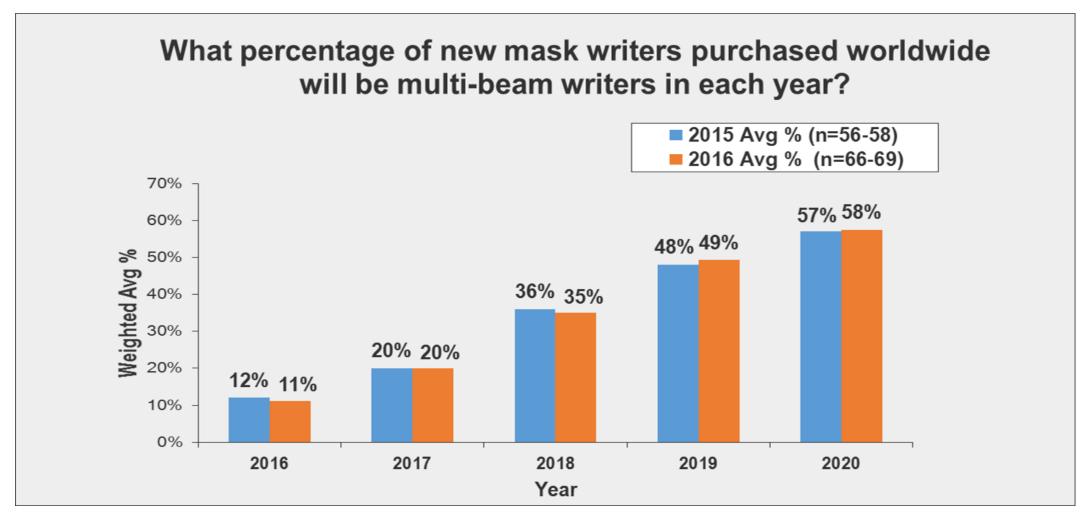


D2S note: Written on IMS alpha machine

Multi-beam exposure without loss of TPT

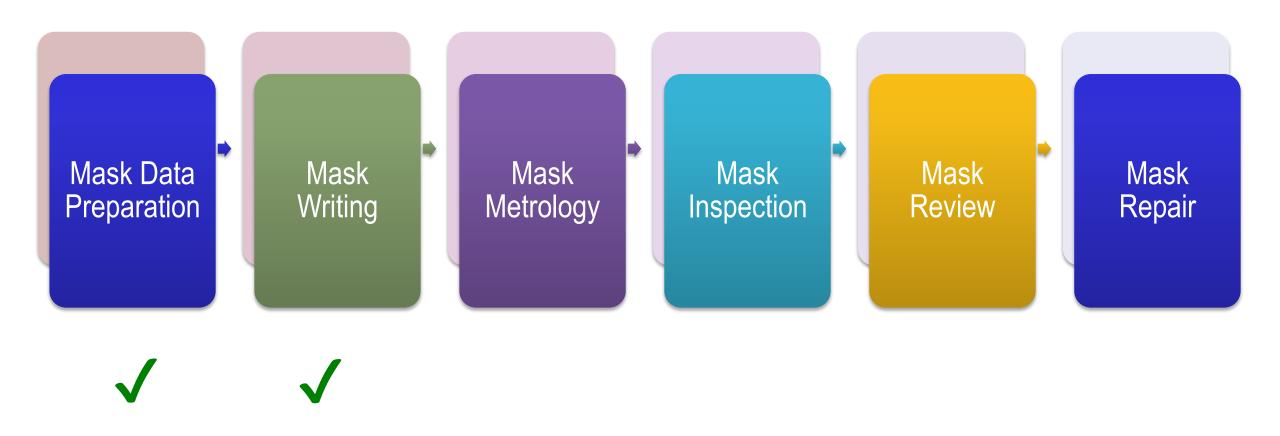
But VSB, Multi-beam Will Co-exist for Years





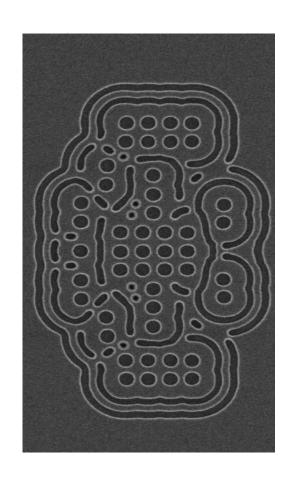
Source: 2016 eBeam Initiative Perceptions Survey www.ebeam.org







The New ILT World Calls for New CD Metrology: Mask and Wafer!

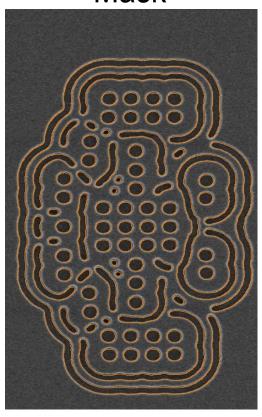


$\widehat{D_{2S}}$

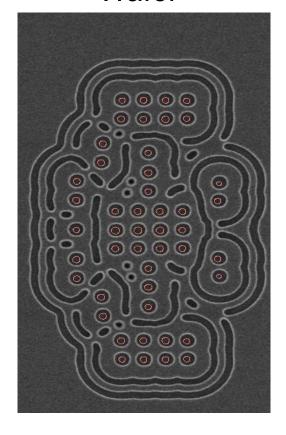
The New ILT World Calls for New CD Metrology:

Mask and Wafer!

Mask



Wafer





Simulation Can Provide Aerial Image from High-Resolution SEM Image

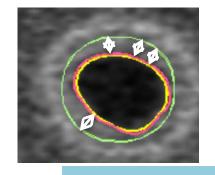
SEM Contour SEM Image Aerial Image Aerial Image **SEM Contour** Simulation Extraction

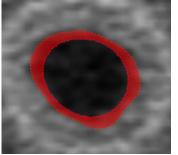


The New ILT World Calls for New CD Metrology:

Mask and Wafer!

Mask



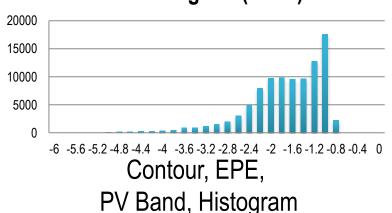


Wafer

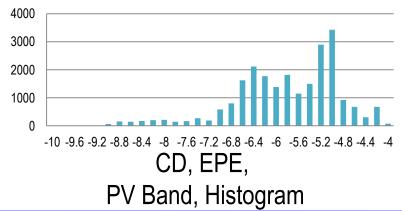


GPU = Real-time for mask + wafer

EPE Histogram (Mask)



EPE Histogram (Wafer)













KT Teron™ 630

Selectable imaging modes to provide the necessary signal-to-noise ratio (SNR) to ensure defect-free 1Xnm generation reticles, whether optical reticles with complex OPC or EUV reticles (Source: KT website)



Applied AERA™4

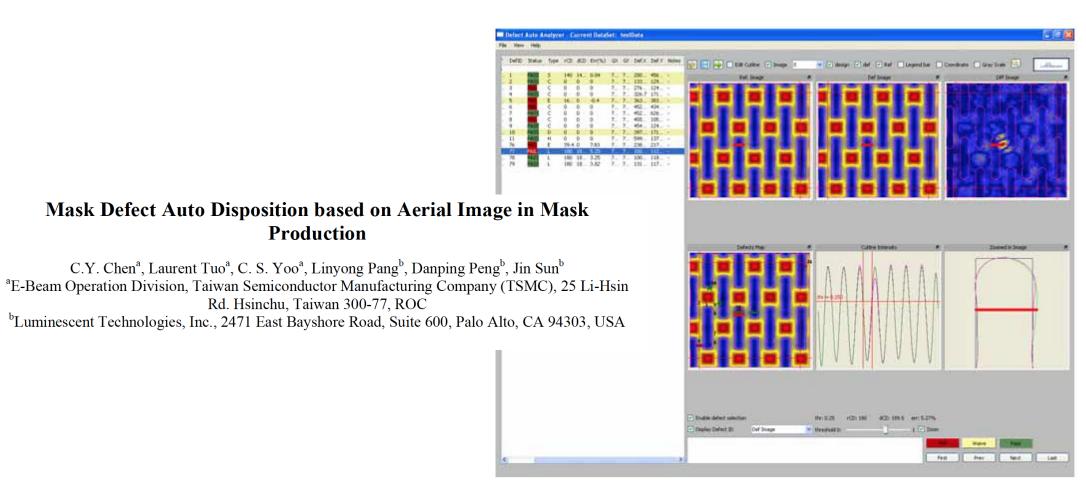
Designed to emulate a scanner, the Aera4 system delivers superior first-time inspection success rate over other high-resolution inspection systems on advanced masks, including those with aggressive OPC, such as inverse lithography. (Source: AMAT website)





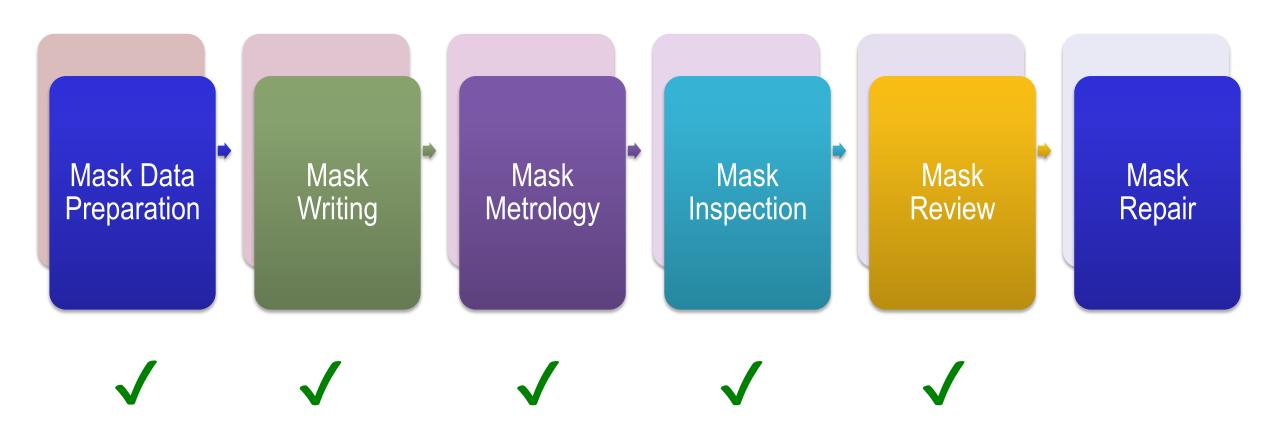


Simulation and Aerial-based Defect Review Has been Used in Production For Years



Ref: C. Y. Chen, et al., "Mask defect auto disposition based on aerial image in mask product", Proc. SPIE 7379, Photomask and Next-Generation Lithography Mask Technology XVI, 73791F (May 11, 2009); doi:10.1117/12.824292; http://dx.doi.org/10.1117/12.824292

$\widehat{D_2S}$

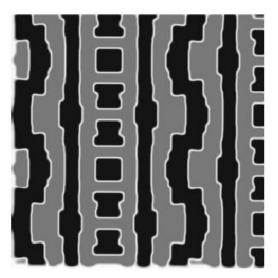


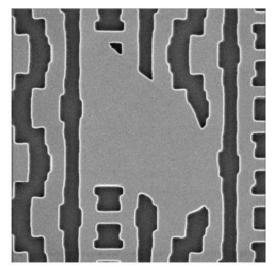


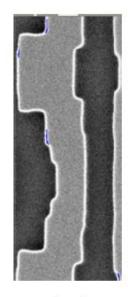
2D Mask Repair, Simulation-based Mask Repair Verification Used in Production For Years

Expanding the Applications of Computational Lithography & Inspection (CLI) in Mask Inspection, Metrology, Review, and Repair

Linyong Pang, Danping Peng, Peter Hu, Dongxue Chen, Lin He, Ying Li, Chris Clifford, Vikram Tolani
Luminescent Technologies, Inc. 2471 East Bayshore Road, Suite 600,
Palo Alto, CA 94303, USA







Rendered Image

Acquired Image

Difference in clean area

(blue)

Ref: L. Pang, et al., "Expanding the Applications of Computational Lithography & Inspection (CLI) in Mask Inspection, Metrology, Review, and Repair", Proc. of SPIE 7971 79712A-1

$\widehat{D_2S}$

2D Mask Repair, Simulation-based Mask Repair Verification Used in Production For Years

In-situ Repair Qualification by Applying Computational Metrology and Inspection (CMI) Technologies

C.Y. Chen^a, Ivan Wei^a, Laurent Tuo^a, C. S. Yoo^a, Dongxue Chen^b, Danping Peng^b, Masaki Satake^b, Bo Su^b, Linyong Pang^b

^aE-Beam Operation Division, Taiwan Semiconductor Manufacturing Company (TSMC), 25 Li-Hsin Rd. Hsinchu, Taiwan 300-77, ROC

^bLuminescent Technologies, Inc., 2300 Geng Road, Suite 250, Palo Alto, CA 94303, USA

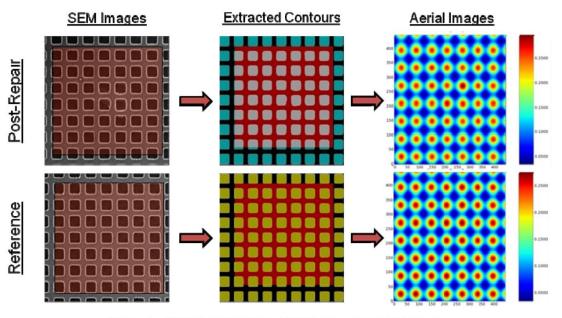


Figure 4 – IRQ data flow from SEM images to aerial images

Ref: C. Y. Chen, et al., "In-situ Repair Qualification by Applying Computational Metrology and Inspection (CMI) Technologies", Proc. of SPIE Vol. 8701 870108-11

The Entire Mask Supply Chain is Ready for



Mask Data Preparation

- MB & handle CL
 - MRC
 - MDP: OLS
 - MV

Mask Writing

Curvilinear ILT Masks

- VSB: Overlapped shots
- Multi-beam

Mask Metrology

- Contour and EPE
- Wafer Plane Analysis

Mask Inspection

- Contour based
- MPI and WPI

Mask Review

- AIMS
- AIA: D2D, D2DB

Mask Repair

 Reference Pattern Generation













